	No.4661	<b>2SA1881/2SC4983</b> PNP/NPN Epitaxial Planar Silicon Transistors Low-Frequency General-Purpose Amp Applications

### Applications

- AF power amp, medium-speed switching, small-sized motor drivers and LED drivers.

### Features

- Large current capacity.
- Low collector to emitter saturation voltage.
- Very small-sized package permitting 2SA1881/2SC4983-applied sets to be made smaller and slimmer.

( ) : 2SA1881

### Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	$V_{CBO}$	(- )15	V
Collector-to-Emitter Voltage	$V_{CEO}$	(- )15	V
Emitter-to-Base Voltage	$V_{EBO}$	(- )5	V
Collector Current	$I_C$	(- )1	A
Collector Current(Pulse)	$I_{CP}$	(- )3	A
Base Current	$I_B$	(- )200	mA
Collector Dissipation	$P_C$	250	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)12V, I_E = 0$			(- )100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(- )100	nA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2V, I_C = (-)50mA$	135※		600※	
	$h_{FE}(2)$	$V_{CE} = (-)2V, I_C = (-)800mA$	80			
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)2V, I_C = (-)50mA$		(300)200		MHz
C-E Saturation Voltage	$V_{CE(sat)}(1)$	$I_C = (-)5mA, I_B = (-)0.5mA$		(- )10	(- )25	mV
	$V_{CE(sat)}(2)$	$I_C = (-)500mA, I_B = (-)25mA$		(- )120	(- )240	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500mA, I_B = (-)25mA$		(- )0.9	(- )1.2	V
Output Capacitance	$C_{ob}$	$V_{CB} = (-)10V, f = 1MHz$		(15)10		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(- )15			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(- )15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(- )5			V

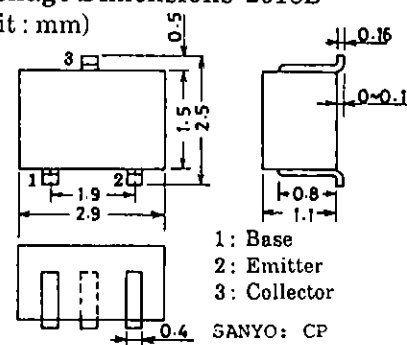
※ : The 2SA1881/2SC4983 are classified by 50mA  $h_{FE}$  as follows:

135	5	270	200	6	400	300	7	600
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Marking : 2SA1881 : IS  
2SC4983 : KN

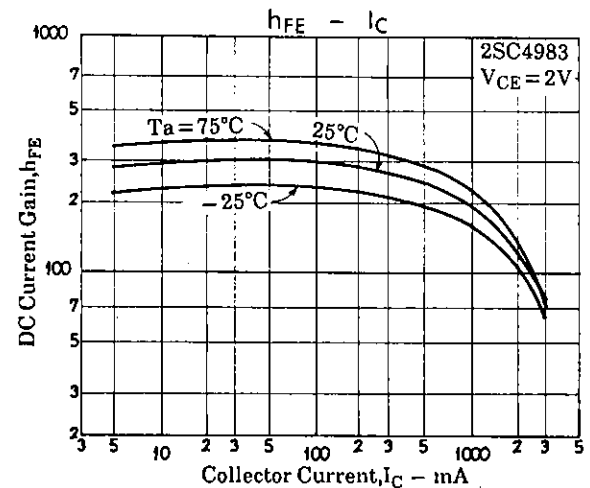
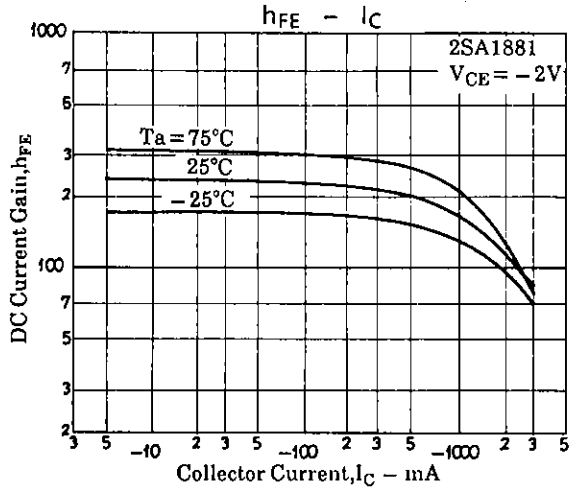
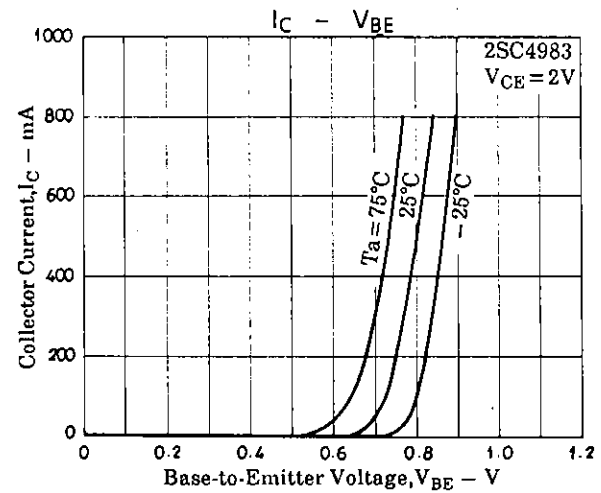
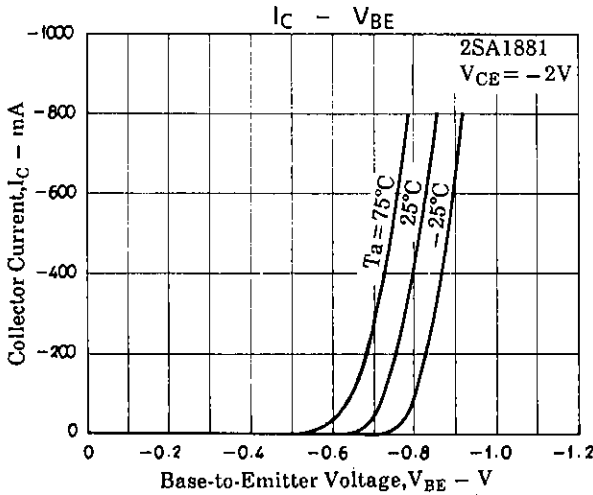
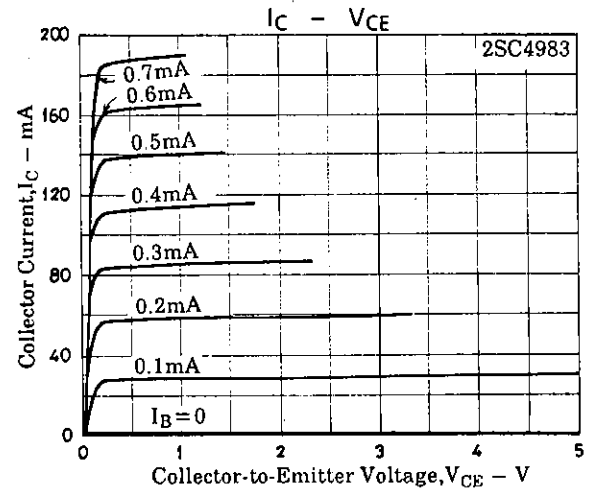
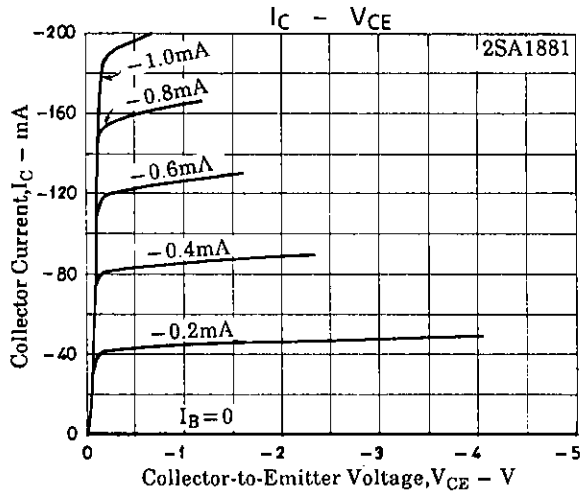
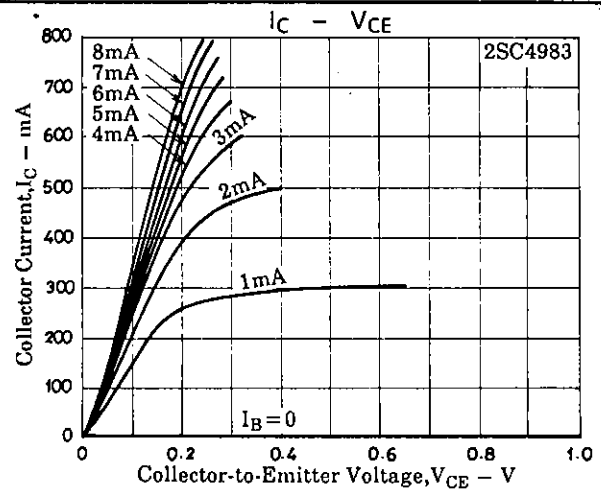
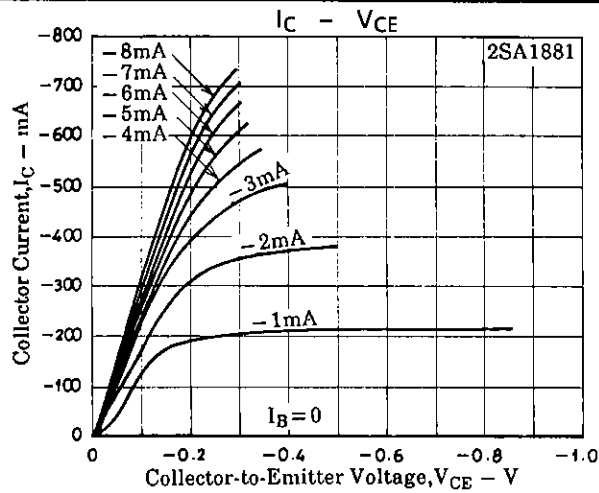
### Package Dimensions 2018B

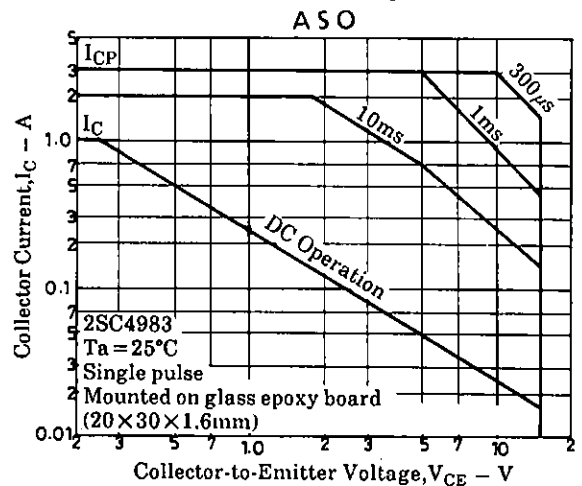
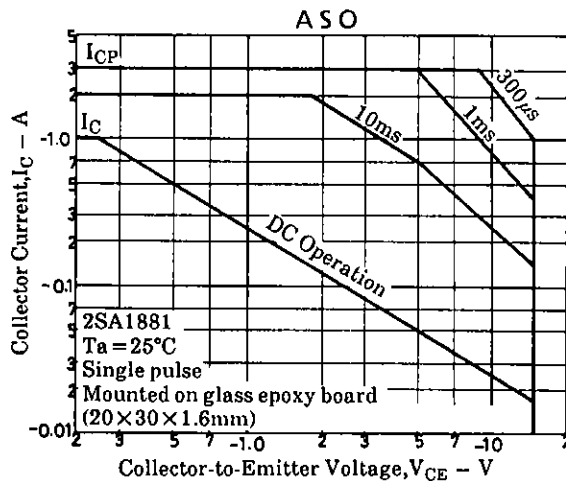
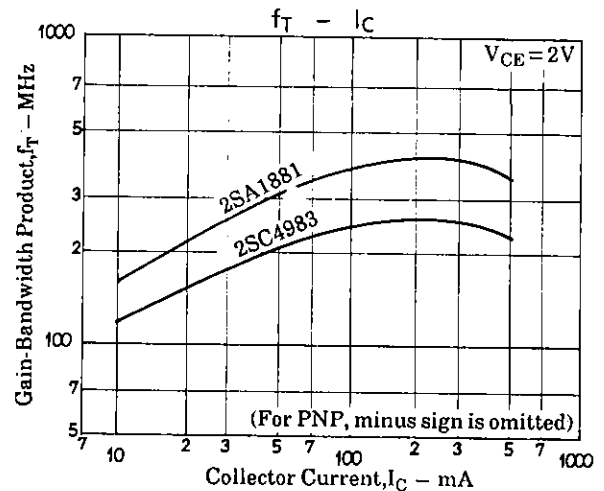
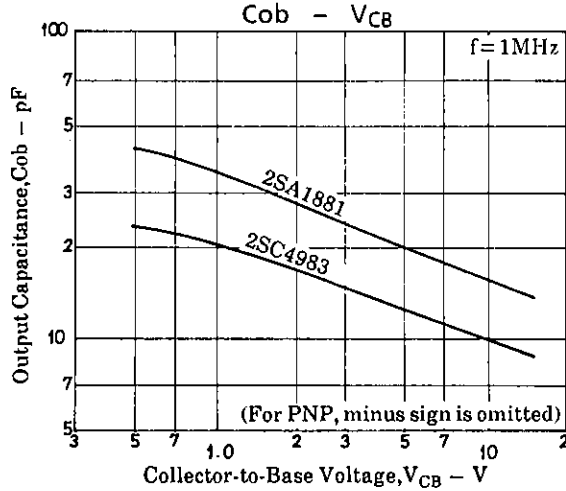
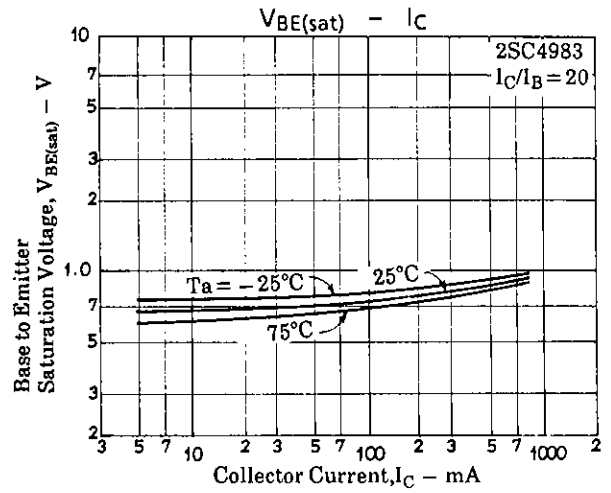
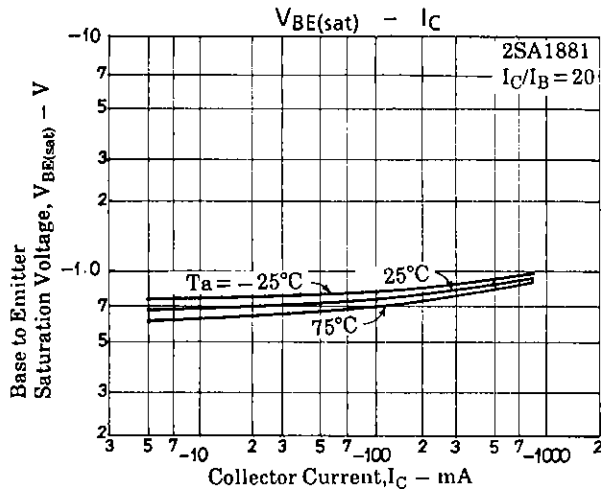
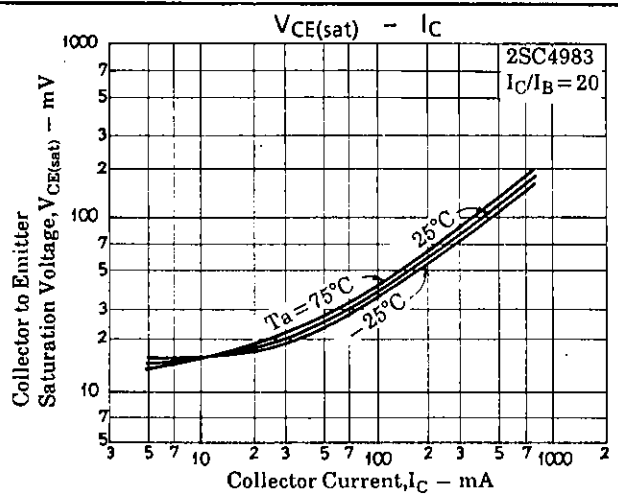
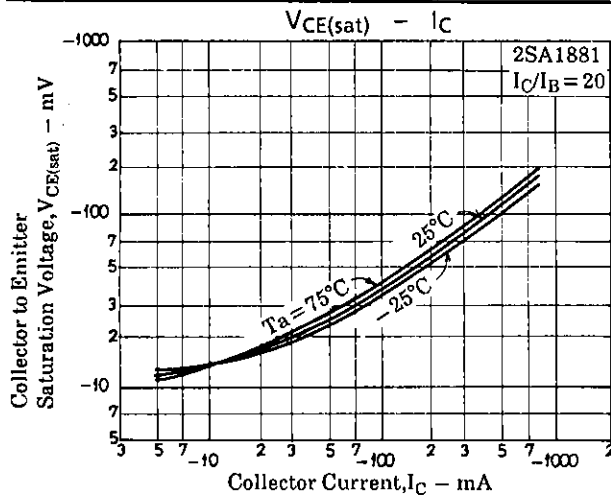
(unit : mm)

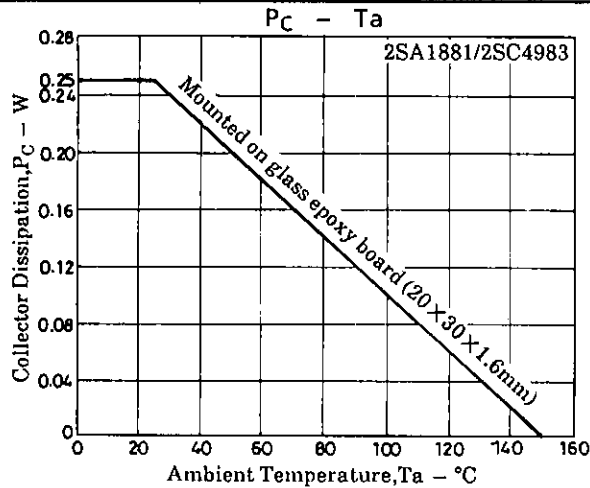


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